

ABSTRACT

Disclosed are an etching or deposition method for a wafer, a method for acquiring a model, and a semiconductor process apparatus, which specifically relate to a temperature control method for temperature control zones of a multi-temperature-zone electrostatic chuck or a multi-temperature-zone heating pedestal. According to the temperature control method, in combination with temperature sensitivity and influences of diffusion and distribution of etching byproducts or deposits with temperature gradient on etching or deposition rates, etching or deposition rate distribution data of positions of the wafer at any target temperature of the temperature control zones can be more accurately predicted. Or by adjusting target temperature control values of the temperature control zones according to target etching or deposition rate distribution data, etching or deposition uniformity of the wafer can be improved, or a desired profile of a surface of the wafer can be obtained.